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Physical Review. B

volume 72

number 12

page range 121307(R)

year 2005

URL http://hdl.handle.net/10097/53199
Polarized light emission from antiphase boundaries acting as slanting quantum wells in GaP/InP short-period superlattices

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(Received 15 June 2005; published 23 September 2005)

Optical properties of anti-phase boundaries (APBs) in monolayer superlattices of GaP/InP are studied. Determining selectively the arrangements of In and Ga atoms around APBs by cross-sectional scanning tunneling microscopy, it is found that atomic layers of InP on (111) and (1010), sandwiched between the domains of superlattices, are formed on APBs. Polarized cathodoluminescence spectroscopy in a transmission electron microscope suggested that the InP layers act as quantum wells oriented on a slant with respect to the substrate and they emit light linearly polarized parallel to the layers.

DOI: 10.1103/PhysRevB.72.121307 PACS number(s): 78.67.De, 68.35.Ct, 68.37.Ef, 78.60.Hk

Crystalline structures in nonequilibrium states such as superlattices (SLs) and quantum wells (QWs), that may possess many useful properties,1 can be produced in semiconductors, spontaneously or artificially, by modern crystal-growth techniques, i.e., metalorganic chemical-vapor deposition (MOVPE), etc. During the growth, structural imperfections, such as defects [e.g., anti-phase boundaries (APBs), stacking faults, etc.] and composition modulation, are frequently formed, and they can affect the electronic properties in device products made of the semiconductors. For example, atomistic structure of imperfect short-period SLs has been intensively examined.2–4 However, such structure has not been fully verified due to experimental difficulties. This paper demonstrates that they can be determined quantitatively by cross-sectional scanning tunneling microscopy (XSTM) combined with polarized cathodoluminescence (CL) spectroscopy in a transmission electron microscope.

Here atomistic structure in a short-period SL structure grown spontaneously in GaInP alloys,5 as well as in other group III-V6 and II-IV7 ternary semiconductor alloys, are studied. The alloy is comprised of monolayer SLs of Ga(1−h)InhP2/Ga(1−h)InhP2 along [111] and [111],5 where the order parameter h can be controlled by varying growth conditions. APBs, at which the sequence of Ga-rich and In-rich layers is 180° out of phase,8 are inevitably introduced during the spontaneous growth of such SLs, and emission lines with photon energies lower than the band gap energy Eg, showing signatures of quantum confinement, are observed in the SLs including APBs. The origin of this emission has been studied by optical spectroscopy with high spatial resolution combined with transmission electron microscopy (TEM) (see Refs. 6–8 and references therein). With some experimental11 and theoretical12 results, an atomic structure of the origin was conjectured; it was associated with APBs. On the contrary, another experiment suggested that the emission is related to defects except APBs.9,10 The reason for the contradiction is that those workers could not obtain experimentally structural data of the APBs at an atomistic level. The atomic structure of APBs was hardly determined with TEM images on which a number of APBs expanding three dimensionally are projected. Their nature was also examined by XSTM,13,14 even though it was not fully explored. This paper suggests that the low-energy emission arises from QWs grown spontaneously on APBs. The arrangements of In and Ga atoms around APBs were observed selectively by XSTM, and atomic layers of InP on APBs, sandwiched between SLs, were observed. The optical data obtained by polarized CL spectroscopy were consistently explained with the model that the InP layers on APBs act as QWs and they emit light linearly polarized parallel to the layers. These results may help to obtain a comprehensive insight into atomistic structures of imperfections in nonequilibrium structures as well as to explore sources of such imperfections.

The sample was an undoped Ga0.3In0.7P layer (1 μm thick) on a GaAs substrate grown by MOVPE (the growth temperature of 650 °C, growth rate of 0.4 nm/s, III/V ratio of 370). The substrate was 2° off from (001) towards [110], so SLs along [111] were mainly formed.15 A small chip of the sample was installed into an ultrahigh vacuum (UHV) scanning tunneling microscope (JEOL, JST-4500T), and then cleaved at a UHV of 1 × 10−8 Pa so as to make a clean (110) surface. A W tip etched electrochemically was approached on a GaInP SL with a UHV scanning electron microscope.16 XSTM images were obtained at room temperature by the constant-current mode (a set current of about 100 pA). A sample voltage of about +3 V was used so as to image the empty-state density associated with In and Ga atoms. Polarized CL spectra and TEM images were obtained simultaneously17 from a (110) cross section (about a few hundred nm thick) of the sample, at the temperature of about 20 K. A beam of 80 keV electrons was used for fear of varying the atomistic structure of GaInP SLs.18 The probe size of a beam for the spectroscopy was about 200 nm, and the spatial resolution was estimated to be about 350 nm. The effect of magnetic field in the microscope (about 1 T) on p-CL spectra is believed to be negligible for GaInP SLs.20

Figure 1(a) shows a XSTM image of GaInP SLs. A centered rectangular net was observed [Fig. 1(c)]. The diamond in Fig. 1(c) denotes a primitive mesh unit of the c(2 × 2) structure; the length of a side is about 6.9 Å, and the obtuse angle is about 110°. A GaAs surface on the same specimen was subsequently examined, and the well-known p(1 × 1) structure21 was observed (not shown). Analyses of the
Bonded to two In atoms. The dot on the net points was explained as a topmost P atom shown schematically in Fig. 1.

XSTM images revealed that the bright dots in Fig. 1, corresponding model of a SL. The bright dots in (d) arrange on diperiodic nets. (f) Height profiles along (a), (b), (c)–(e), and (a)–(d) in (c). (g) The corresponding model for GaInP SL.

XSTM images revealed that the c(2 × 2) mesh unit is defined by two fundamental translation vectors along [112] and [¯112]. It is believed that the heights on XSTM images of GaInP SLs are determined by two factors, i.e., the difference of the bond length for In–P to that for Ga–P and the band offset at the InP/GaP interface, and so the height of the nth In layer, nearby the surface, would be higher than that of the nth Ga layer on empty-state images. Figure 1(g) shows the corresponding model of a SL. The bright dots in Fig. 1(c), that have the same height as the dot at a, represent In atoms in the first layer [Fig. 1(d)]. The first In layer is about 0.4 Å higher than the first Ga layer [Fig. 1(f)], and the distance from the first In layer to the second In layer (about 0.6 Å2) is smaller than that to the second Ga layer (about 0.8 Å) [Fig. 1(f)]. The arrangement of In atoms in the first layer was also observed on an image of the inverse fast Fourier transform (FFT) of the spots marked by the arrows in Fig. 1(b) (not shown). Similar c(2 × 2) structures were observed on filled-state images, and a bright dot on the net points was explained as a topmost P atom bonded to two In atoms.

APBs were observed on XSTM images. For example, as shown schematically in Fig. 1(e), the sequence of In rows along [112] (as a guide, see the solid lines) was 180° out of phase at the atomic row, along [110], indicated by the arrows. The row did not consist of the sequence of In–Ga–...
APBs was observed. Dark black bands extended nearly along \( \{1\overline{1}1\} \) were APBs, and the geometry of a band was similar to that of the long-extended APB on XSTM images. Light gray bands nearly along \{001\} were presumably associated with the short APBs, as well as disordered zones, observed by XSTM. Since many parts of the bands were narrow, many planar segments of APBs were nearly perpendicular to \( (1\overline{1}0) \), in the thin TEM specimen. The TEM specimen emitted CL light with photon energy of \( E_{\text{g}}=1.90 \text{ eV} \) [Fig. 3(b)], due to the band-to-band transition in SLs. The order parameter was estimated that \( h=0.47 \) with an empirical formula, and the estimated value was comparable to the XSTM data. Similar TEM and CL data were obtained from any area in the specimen. The left figure shows a dark-field TEM image of a specimen obtained from a SL reflection. The encircled area is characterized. A CL light emitted from the specimen is reflected on an ellipsoidal mirror and the reflected light is transmitted in a linear polarizer. The transmission direction of the polarizer for electric field is determined by the rotation angle \( \phi \). Then, the transmitted light is collected into a charge couple device detector through a monochromator. (b) Polarized CL spectra for various \( \phi \). (c) CL intensities vs \( \phi \). The solid or broken curve is a calculated CL intensity for the QW on \( (1\overline{1}0) \) or \( (1\overline{1}1) \), respectively.

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mental method will be used for discovering and quantitative understanding of novel optical properties of various kinds of nanostructures.

This work was partially supported by the Ministry of Education, Science, Sports and Culture, Grant-in-Aid for Young Scientist (A)(2) No.15681006, 2003-2005. GaInP SLs were provided by Mitsubishi Chemical Co. I am indebted to Professor S. Takeda for use of the facilities and for fruitful discussion.

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